TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

# 2SA1681

## **Power Amplifier Applications Power Switching Applications**

- Low saturation voltage:  $V_{CE}$  (sat) = -0.5 V (max) (I<sub>C</sub> = -1 A)
- High speed switching time:  $t_{stg} = 300 \text{ ns}$  (typ.)
- Small flat package
- $P_C = 1.0$  to 2.0 W (mounted on ceramic substrate)
- Complementary to 2SC4409

### Maximum Ratings (Ta = 25°C)

| Characteristics             | Symbol           | Rating     | Unit |  |
|-----------------------------|------------------|------------|------|--|
| Collector-base voltage      | V <sub>CBO</sub> | -60        | V    |  |
| Collector-emitter voltage   | V <sub>CEO</sub> | -50        | V    |  |
| Emitter-base voltage        | V <sub>EBO</sub> | -6         | V    |  |
| Collector current           | Ι <sub>C</sub>   | -2         | А    |  |
| Base current                | Ι <sub>Β</sub>   | -0.2       | А    |  |
| Collector power dissipation | P <sub>C</sub>   | 500        | mW   |  |
|                             | P <sub>C</sub>   | 1000       |      |  |
|                             | (Note)           | 1000       |      |  |
| Junction temperature        | Tj               | 150        | °C   |  |
| Storage temperature range   | T <sub>stg</sub> | -55 to 150 | °C   |  |

|  |                                      | L                                  | Jnit: mm          |
|--|--------------------------------------|------------------------------------|-------------------|
| $ \begin{array}{c c}     1 \\     \hline     1 \\     \hline     0.45 - 0.05 \\     \hline     0.4 - 0.05 \\     \hline     1.5 \pm 0.1 \\     \hline     1 \\     1.5 \pm 0.1 \\     \hline     1   \end{array} $ | rti th<br>2 3<br>use<br>ollector (he | 0.8MIN<br>-2.5 ± 0.1<br>-2.5 ± 0.1 | 1.6MAX.<br>± 0.05 |
| PW-MINI  |                                      |                                    |                   |
| JEDEC  |                                      | _                                  |                   |
| JEITA  | S                                    | C-62                               |                   |
| TOSHIBA  | 2-                                   | 5K1A                               |                   |

Weight: 0.05 g (typ.)

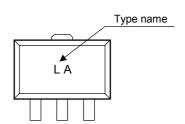
Note: Mounted on ceramic substrate (250 mm<sup>2</sup> × 0.8 t)



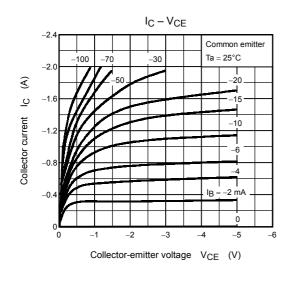
Electrical Characteristics (Ta = 25°C)

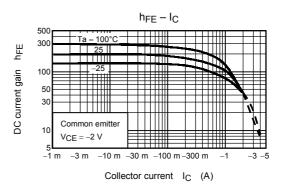
| Charac                              | teristics           | Symbol                         | Test Condition   | Min | Тур. | Max  | Unit |
|-------------------------------------|---------------------|--------------------------------|--|-----|------|------|------|
| Collector cut-off cur               | rrent               | I <sub>CBO</sub>               | $V_{CB} = -60 \text{ V}, \text{ I}_{E} = 0$  | —   | _    | -0.1 | μA   |
| Emitter cut-off current             |                     | I <sub>EBO</sub>               | $V_{EB} = -6 V, I_C = 0$   | _   | _    | -0.1 | μA   |
| Collector-emitter breakdown voltage |                     | V (BR) CEO                     | I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0  | -50 |      | _    | V    |
| DC aurrent gain                     | h <sub>FE (1)</sub> | $V_{CE} = -2 V, I_C = -100 mA$ | 120  | _   | 400  |      |      |
| DC current gain                     |                     | h <sub>FE (2)</sub>            | V <sub>CE</sub> = -2 V, I <sub>C</sub> = -1.5 A  | 40  | _    | _    |      |
| Collector-emitter sa                | aturation voltage   | V <sub>CE (sat)</sub>          | I <sub>C</sub> = 1 A, I <sub>B</sub> = -0.05 A   | —   | _    | -0.5 | V    |
| Base-emitter saturation voltage     |                     | V <sub>BE (sat)</sub>          | I <sub>C</sub> = 1 A, I <sub>B</sub> = -0.05 A   | —   | _    | -1.2 | V    |
| Transition frequency                |                     | f <sub>T</sub>                 | $V_{CE} = -2 V, I_C = -100 mA$   | _   | 100  | _    | MHz  |
| Collector output capacitance        |                     | C <sub>ob</sub>                | V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz   | _   | 23   | _    | pF   |
| Switching time S                    | Turn-on time        | t <sub>on</sub>                | $I_{B1} \bigoplus_{20 \ \mu s} I_{B2} \bigoplus_{I_{B1}} \bigcup_{I_{B1}} \bigcup_{I$ | _   | 0.1  | _    |      |
|                                     | Storage time        | t <sub>stg</sub>               |  | _   | 0.3  | _    | μs   |
|                                     | Fall time           | t <sub>f</sub>                 | -I <sub>B1</sub> = I <sub>B2</sub> = 0.05 A,<br>DUTY CYCLE ≤ 1%  | _   | 0.1  | _    |      |

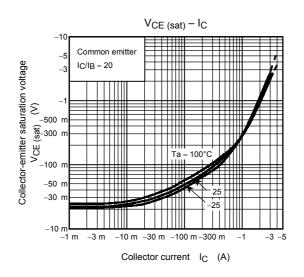
# Marking

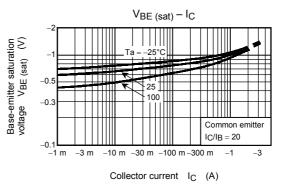


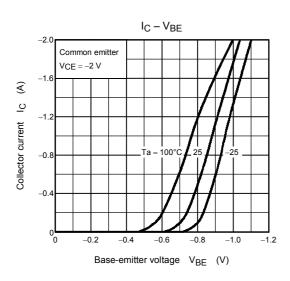
# **TOSHIBA**

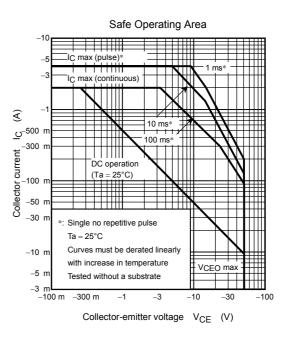












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